

## IR20153S & (PbF)

### HIGH SIDE DRIVER WITH RECHARGE

#### Features

- Floating channel designed for bootstrap operation  
 Fully operational up to 150V  
 Tolerant to negative transient voltage, dV/dt immune
- Gate drive supply range from 5V to 20V
- Undervoltage lockout
- Internal recharge FET for bootstrap refresh
- Internal deadtime of 11 $\mu$ s and 0.8 $\mu$ s
- CMOS Schmitt-triggered input logic
- Output out of phase with input
- Reset input
- Split pull-up and pull-down gate drive pins
- Also available LEAD-FREE (PbF)

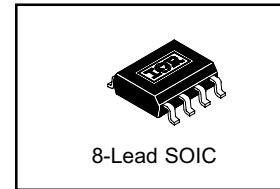
#### Product Summary

$V_{\text{OFFSET}}$	150V max.
$I_{\text{O}+/-}$	400mA @ $V_{\text{BS}}=7\text{V}$ , 1.5A @ $V_{\text{BS}}=16\text{V}$
$V_{\text{OUT}}$	5-20V
$t_{\text{on/off}}$	1.0 and 0.3 $\mu$ s

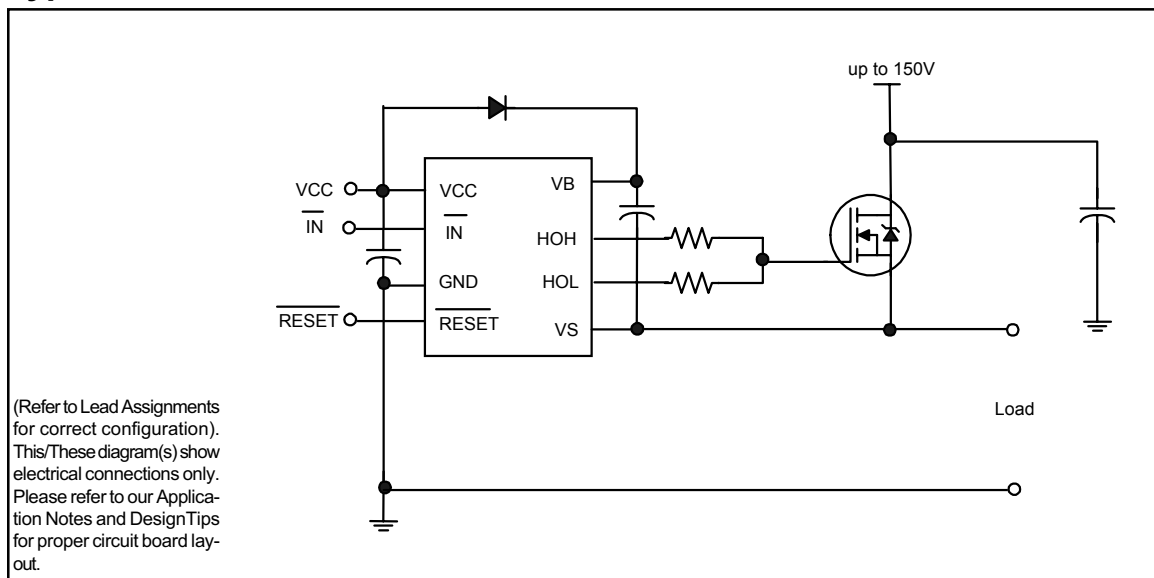
#### Description

The IR20153S is a high voltage, high speed power MOSFET driver. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is compatible with standard CMOS output down to 3.3V. The output driver features a high pulse current buffer stage designed for minimum cross-conduction. The floating channel can be used to drive an N-channel power MOSFET in the high or low side configuration which operates up to 150 volts.

#### Package



#### Typical Connection



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## Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to GND, all currents are defined positive into any lead. This is a stress only rating and operation of the device at these or any conditions exceeding those indicated in the operational sections of this specifications is not implied.

Symbol	Definition	Min.	Max.	Units
V <sub>B</sub>	High side driver output stage voltage	-5.0	170	V
V <sub>S</sub>	High side floating supply offset voltage	- 8.0	150	
V <sub>HO</sub>	Output voltage gate high connection	V <sub>S</sub> - 0.3	V <sub>B</sub> + 0.3	
V <sub>CC</sub>	Low side fixed supply voltage	-0.3	25	
V <sub>IN</sub>	Input voltage (IN and RESET)		-0.3	V <sub>CC</sub> +0.3
dV/dt	Allowable offset voltage slew rate	—	50	V/nsec
T <sub>J</sub>	Junction temperature	-55	150	°C
T <sub>S</sub>	Storage temperature	-55	150	
T <sub>L</sub>	Lead temperature (soldering, 10 seconds)	—	300	

## Recommended Operating Conditions

The input/output logic timing diagram is shown in Fig. 2. For proper operation the device should be used within the recommended conditions. All voltage parameters are absolute voltages referenced to GND. The V<sub>S</sub> offset rating is tested with all suppliers biased at V<sub>CC</sub>=5V and V<sub>BS</sub>=7V.

Symbol	Definition	Min.	Max.	Units
V <sub>B</sub>	High side driver output stage voltage	V <sub>S</sub> + 5	V <sub>S</sub> + 20	V
V <sub>S</sub>	High side floating supply offset voltage	-1.6	150	
V <sub>HO</sub>	Output voltage gate high connection	V <sub>S</sub>	V <sub>B</sub>	
V <sub>CC</sub>	Supply voltage	5	20	
V <sub>IN</sub>	Input voltage (IN and RESET)	0	V <sub>CC</sub>	
T <sub>A</sub>	Ambient temperature	-55	150	°C

## Electrical Characteristics

Unless otherwise specified,  $V_{CC} = 5V$ ,  $V_{BS} = 7V$ ,  $V_S = 0V$ ,  $I_N = 0V$ ,  $R_{ES} = 5V$ , load  $R = 50\Omega$ ,  $C = 6.8nF$  (see Figure 3).  
Unless otherwise noted, these specifications apply for an operating ambient temperature of  $T_A = 25^\circ C$ .

Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
<b>VCC Supply Characteristics</b>						
$V_{CCUV+}$	VCC supply undervoltage positive going threshold	—	—	4.3	V	$V_{CC}$ rising from 0V
$V_{CCUV-}$	VCC supply undervoltage negative going threshold	2.5	—	—		$V_{CC}$ dropping from 5V
$V_{CCUVHYS}$	VCC supply undervoltage lockout hysteresis	0.01	0.3	0.60		
$I_{QCC}$	VCC supply current	—	—	400	$\mu A$	$V_{CC} = 3.6V$ & $6.5V$
<b>VBS Supply Characteristics</b>						
$V_{BSUV+}$	VBS supply undervoltage positive going threshold	—	—	4.3	V	VBS rising from 0V
$V_{BSUV-}$	VBS supply undervoltage negative going threshold	2.5	—	—		VBS dropping from 5V
$V_{BSUVHYS}$	VBS supply undervoltage lockout hysteresis	0.01	0.3	0.60		
$I_{QBS1}$	VBS supply current	—	—	100	$\mu A$	static mode, $V_{BS} = 7V$ , $I_N = 0V$ or $5V$
$I_{QBS2}$	VBS supply current	—	—	200	$\mu A$	static mode, $V_{BS} = 16V$ , $I_N = 0V$ or $5V$
<b>VB. VS Supply Characteristics</b>						
$I_{LK}$	Offset supply leakage current	—	—	50	$\mu A$	$V_B = V_S = 150V$
<b>Gate Driver Characteristics</b>						
$I_{o+1}$	Peak output source current	250	400	—	mA	
$I_{o+2}$	Peak output source current	800	1500	—	mA	$V_{BS} = 16V$
$t_{r1}$	Output rise time	—	0.2	0.4	$\mu sec$	
$t_{r2}$	Output rise time	—	0.1	0.2	$\mu sec$	$V_{BS} = 16V$
$I_{o-1}$	Peak output sink current	250	400	—	mA	$I_N = 5V$
$I_{o-2}$	Peak output sink current	800	1500	—	mA	$V_{BS} = 16V$ , $I_N = 5V$
$t_{f1}$	Output fall time	—	0.2	0.4	$\mu sec$	$I_N = 5V$
$t_{f2}$	Output fall time	—	0.1	0.2	$\mu sec$	$V_{BS} = 16V$ , $I_N = 5V$
$t_{on}$	Input-to-Output Turn-on propagation delay (50% input level to 10% output level)	—	1.0	2.0	$\mu sec$	
$t_{off}$	Input-to-Output Turn-off propagation delay (50% input level to 90% output level)	—	0.3	0.9	$\mu sec$	
$t_{res,off}$	RES-to-Output Turn-off propagation delay (50% input level to 90% [t <sub>ph</sub> ] output levels)	—	0.3	0.9	$\mu sec$	

## Electrical Characteristics

Unless otherwise specified,  $V_{CC} = 5V$ ,  $V_{BS} = 7V$ ,  $V_S = 0V$ ,  $I_N = 0V$ ,  $R_{ES} = 5V$ , load  $R = 50\Omega$ ,  $C = 6.8nF$  (see Figure 3).

Unless otherwise noted, these specifications apply for an operating ambient temperature of  $T_A = 25^\circ C$ .

Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
<b>Gate Driver Characteristics cont.</b>						
$t_{res,on}$	RES-to-Output Turn-On Propagation Delay (50% input level to 10% [tp] output levels)	-	1.0	2.0	$\mu sec$	
<b>Input Characteristics</b>						
$V_{INH}$	High Logic Level Input Threshold	3	-	-	V	
$V_{INL}$	Low Logic Level Input Threshold	-	-	1.4	V	
$R_{IN}$	High Logic Level Input Resistance	40	100	220	$k\Omega$	
$V_{H\_RES}$	High Logic Level RES Input Threshold	3	-	-	V	
$V_{L\_RES}$	Low Logic Level RES Input Threshold	-	-	1.4	V	
$R_{RES}$	High Logic Level RES Input Resistance	40	100	220	$k\Omega$	
<b>Recharge Characteristics</b> (see Figure 3a)						
$t_{on\_rech}$	Recharge Transistor Turn-On Propagation Delay	7	11	15	$\mu sec$	$V_S = 5V$
$t_{off\_rech}$	Recharge Transistor Turn-Off Propagation Delay	-	0.3	0.9	$\mu sec$	
$V_{RECH}$	Recharge Output Transistor On-State Voltage Drop	-	-	1.2	V	$I_S = 1mA$ , $I_N = 5V$
<b>Deadtime Characteristics</b>						
$D_{THOFF}$	High Side Turn-Off to Recharge gate Turn-On	7	11	15	$\mu sec$	
$D_{THON}$	Recharge gate Turn-Off to High Side Turn-On.	0.4	0.8	1.5	$\mu sec$	

A True table for V<sub>CC</sub>, V<sub>BS</sub>, RESET, IN, H<sub>o</sub> and RechFET is shown as follows. This truth table is for ACTIVE LOW IN.

V <sub>CC</sub>	V <sub>BS</sub>	RESET-	IN-	H <sub>o</sub>	RechFET
<V <sub>CC</sub> UVLO-	<V <sub>BS</sub> UVLO-	HIGH	HIGH	OFF	ON
<V <sub>CC</sub> UVLO-	<V <sub>BS</sub> UVLO-	HIGH	LOW	OFF	ON
<V <sub>CC</sub> UVLO-	<V <sub>BS</sub> UVLO-	LOW	HIGH	OFF	ON
<V <sub>CC</sub> UVLO-	<V <sub>BS</sub> UVLO-	LOW	LOW	OFF	ON
<V <sub>CC</sub> UVLO-	>V <sub>BS</sub> UVLO+	HIGH	HIGH	OFF	ON
<V <sub>CC</sub> UVLO-	>V <sub>BS</sub> UVLO+	HIGH	LOW	OFF	ON
<V <sub>CC</sub> UVLO-	>V <sub>BS</sub> UVLO+	LOW	HIGH	OFF	ON
<V <sub>CC</sub> UVLO-	>V <sub>BS</sub> UVLO+	LOW	LOW	OFF	ON
>V <sub>CC</sub> UVLO+	<V <sub>BS</sub> UVLO-	HIGH	HIGH	OFF	ON
>V <sub>CC</sub> UVLO+	<V <sub>BS</sub> UVLO-	HIGH	LOW	OFF	OFF
>V <sub>CC</sub> UVLO+	<V <sub>BS</sub> UVLO-	LOW	HIGH	OFF	ON
>V <sub>CC</sub> UVLO+	<V <sub>BS</sub> UVLO-	LOW	LOW	OFF	ON
>V <sub>CC</sub> UVLO+	>V <sub>BS</sub> UVLO+	HIGH	HIGH	OFF	ON <sup>1</sup>
>V <sub>CC</sub> UVLO+	>V <sub>BS</sub> UVLO+	HIGH	LOW	ON	OFF <sup>1</sup>
>V <sub>CC</sub> UVLO+	>V <sub>BS</sub> UVLO+	LOW	HIGH	OFF	ON <sup>1</sup>
>V <sub>CC</sub> UVLO+	>V <sub>BS</sub> UVLO+	LOW	LOW	OFF	ON <sup>1</sup>

RESET = HIGH indicates that high side MOSFET is allowed to be turned on.

RESET = LOW indicates that high side MOSFET is OFF.

IN = LOW indicates that high side MOSFET is on.

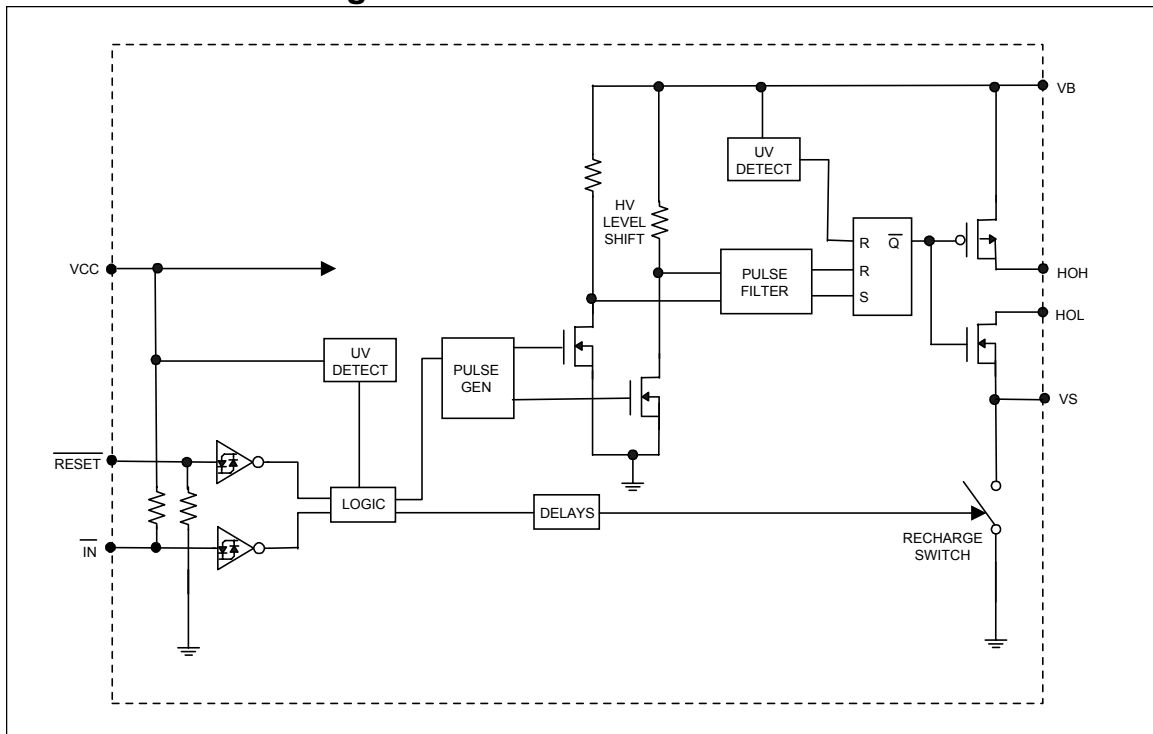
IN = HIGH indicates that high side MOSFET is off.

RechFET = ON indicates that the recharge MOSFET is on.

RechFET = OFF indicates that the recharge MOSFET is off.

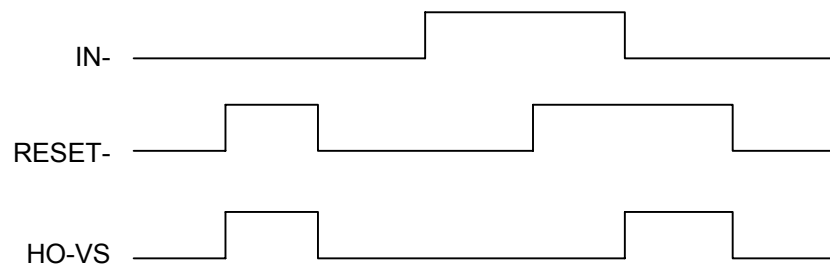
<sup>1</sup>Note: Refer to the RESET functionality graph of Figure 7, for V<sub>CC</sub> and V<sub>BS</sub> voltage ranges under which the functionality is normal.

## Functional Block Diagram

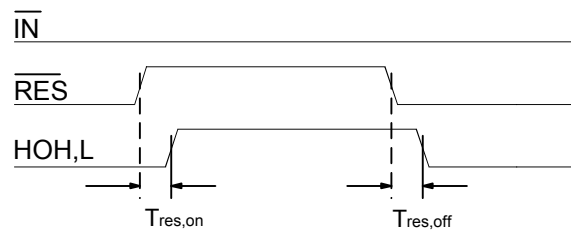


## Lead Definitions and Assignments

Symbol	Description
VCC	Driver Supply
IN-	Driver Control Signal Input
GND	Ground
RESET	Driver Enable Signal Input
VS	MOSFET Source Connection
H <sub>OL</sub>	MOSFET Gate Low Connection
H <sub>OH</sub>	MOSFET Gate High Connection
VB	Driver Output Stage Supply



**Figure 1. Input/Output Functional Diagram**



**Figure 1a. Reset Timing Diagram**

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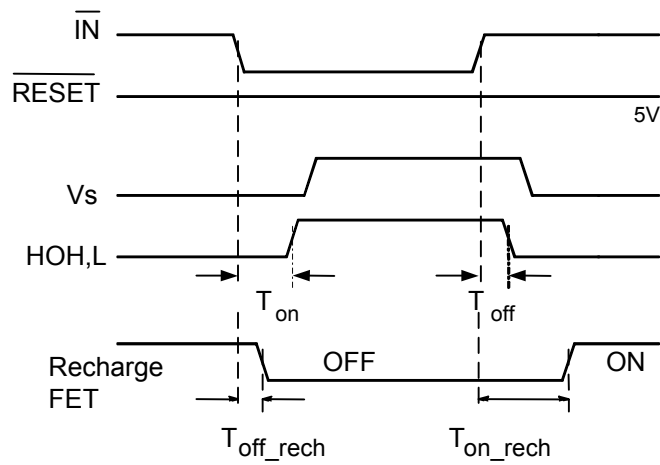


Figure 2. Input/Output Timing Diagram

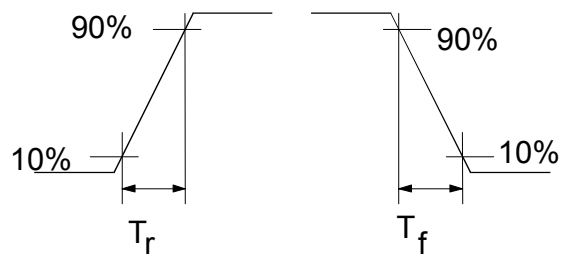


Figure 2a. Output Timing Diagram



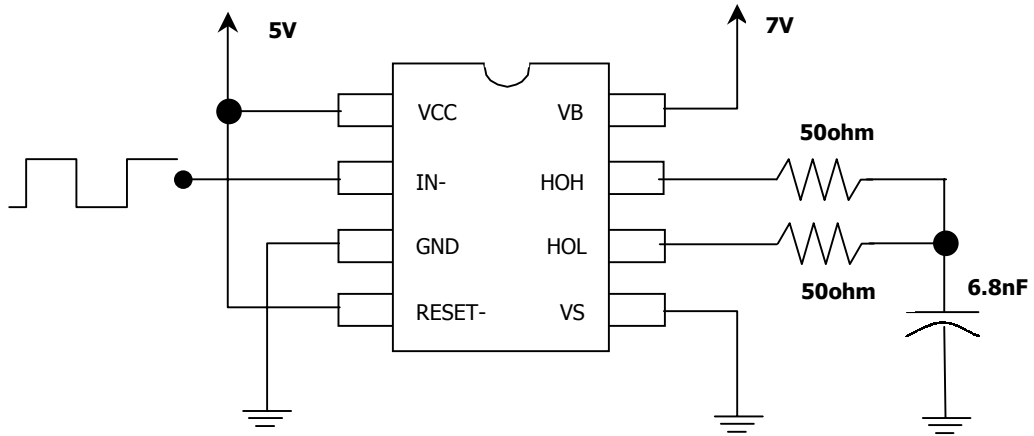


Figure 3. Switching Time Test Circuit

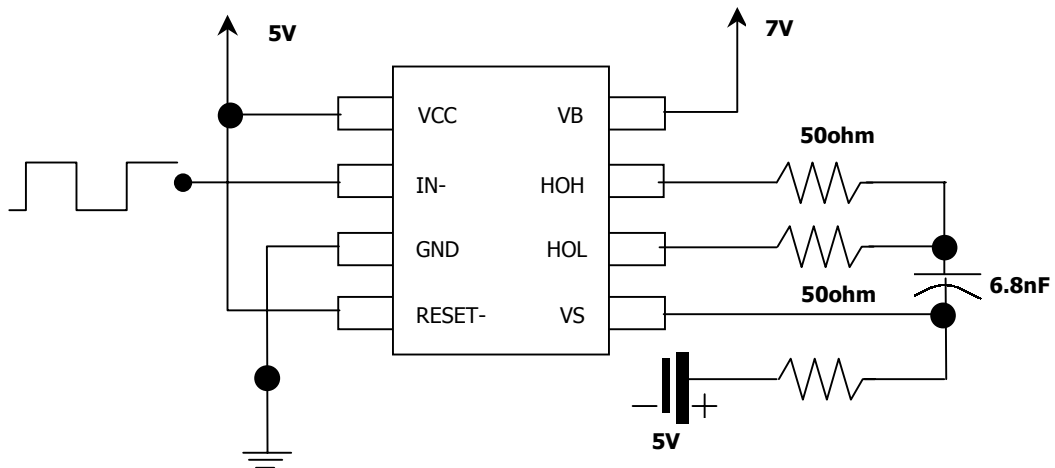
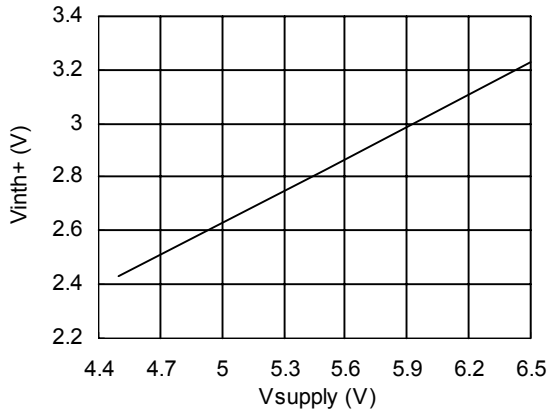
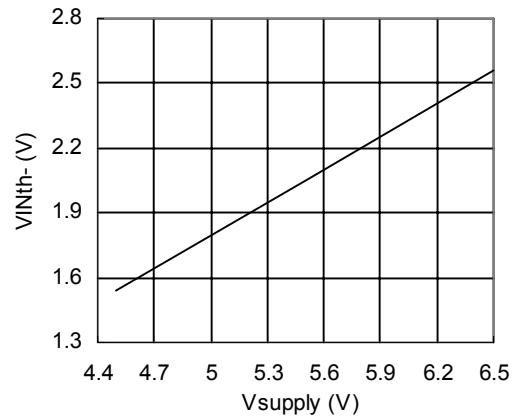


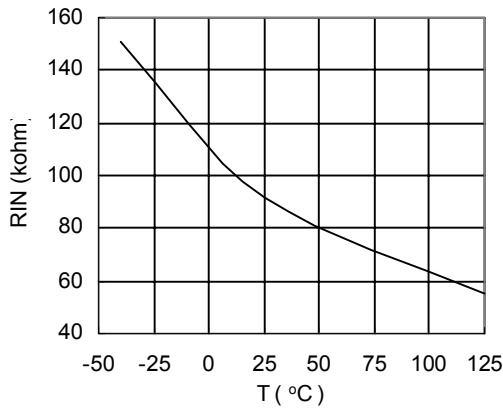
Figure 3a. Ton\_rech and Toff\_rech Test Circuit



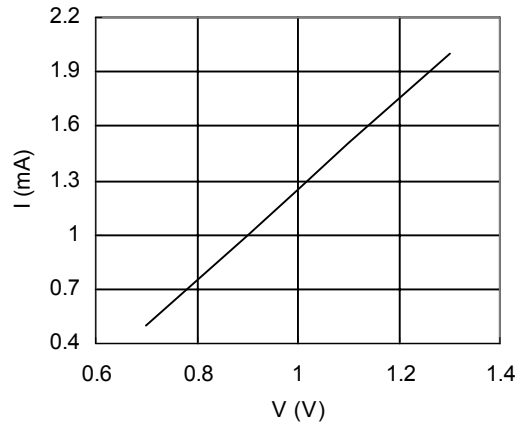
**Figure 4. Positive Input and Reset Threshold Voltage vs. Vsupply**



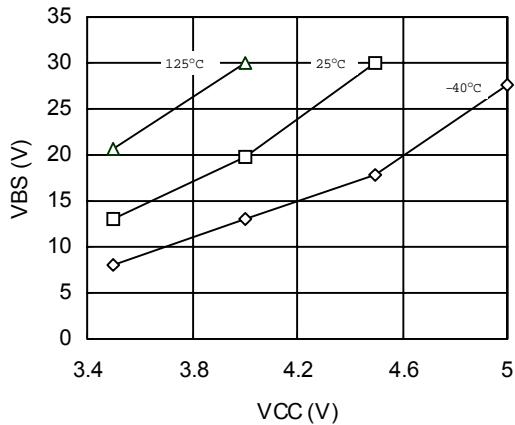
**Figure 5. Negative Input and Reset Threshold Voltage vs. Vsupply**



**Figure 6. Input and Reset Impedance vs. Temperature**

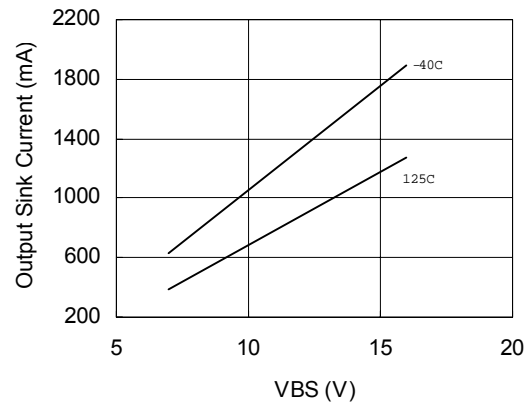


**Figure 7. Recharge FET I-V Curve**

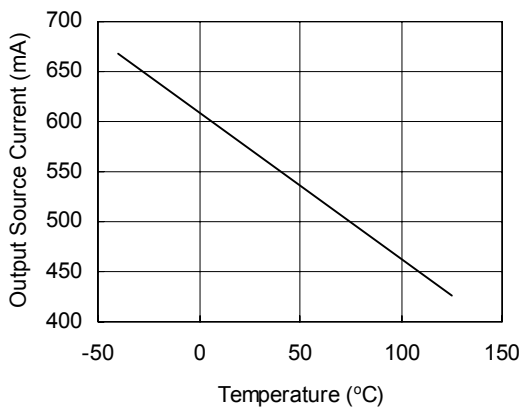


**Figure 8. Reset Functionality**

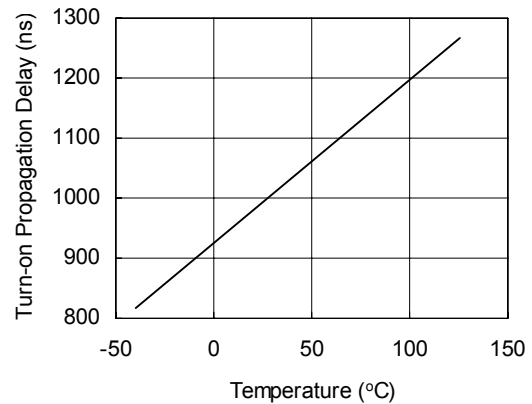
This graph explains the functionality limitation as a function of VCC, VBS and temperature. Each curve on the graph represents VCC Vs. VBS, for a particular temperature. For each particular temperature and VCC, the output is non-functional for any value of VBS above the drawn curve. But for any value of VBS below the curve the functionality is fine.



**Figure 9. Output Sink Current vs. VBS**

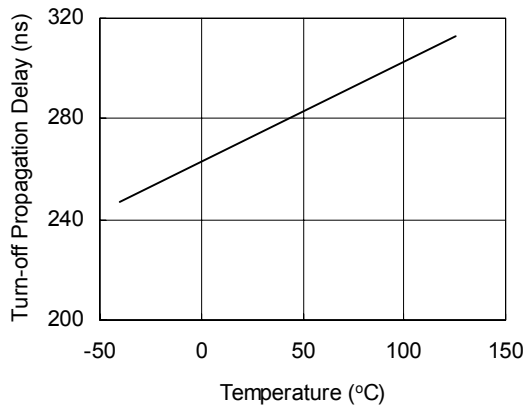


**Figure 10. Output Source Current vs. Temperature, VBS=7V**

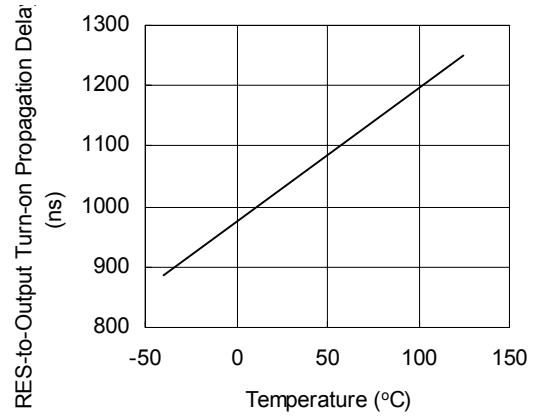


**Figure 11. Turn-on Propagation Delay vs. Temperature, VBS=7V**

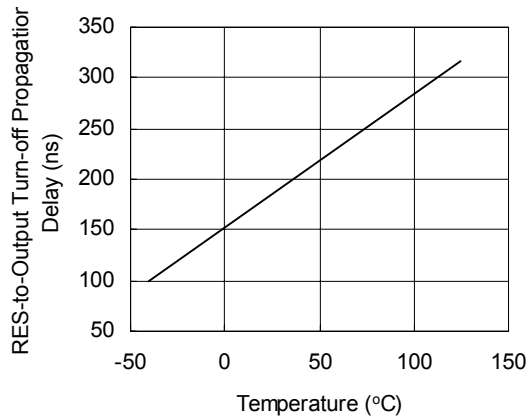
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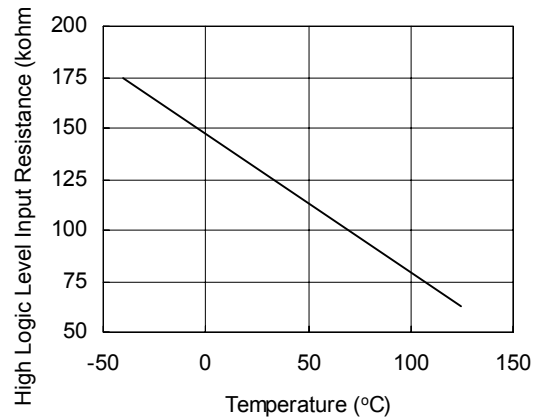
**Figure 12. Turn-off Propagation Delay vs. Temperature, VBS=7V**



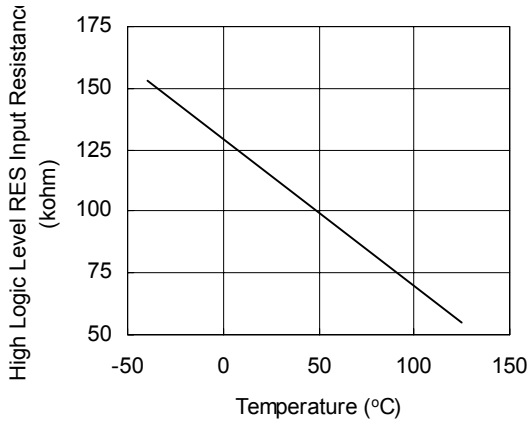
**Figure 13. RES-to-Output Turn-on Propagation Delay vs. Temperature, VBS=7V**



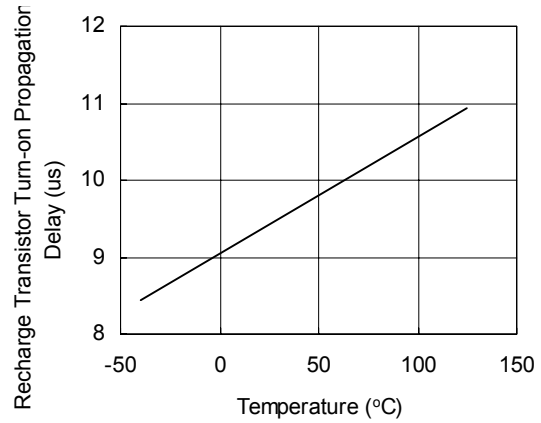
**Figure 14. RES-to-Output Turn-off Propagation Delay vs. Temperature, VBS=7V**



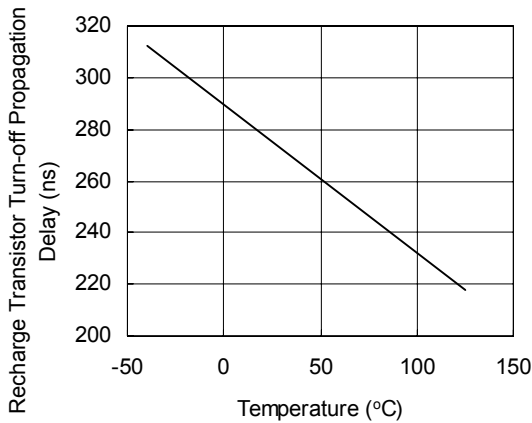
**Figure 15. High Logic Level Input Resistance vs. Temperature, VBS=7V**



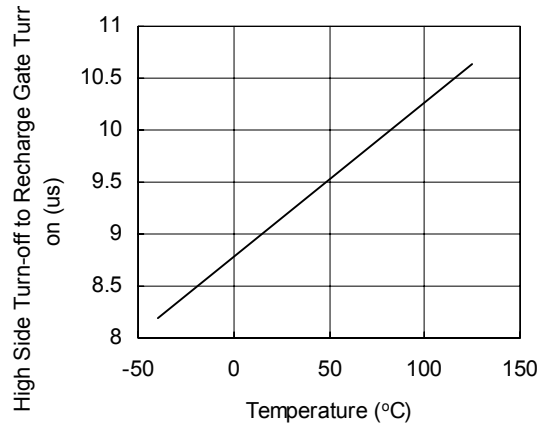
**Figure 16. High Logic Level RES Input Resistance vs. Temperature, VBS=7V**



**Figure 17. Recharge Transistor Turn-on Propagation Delay vs. Temperature, VBS=7V**



**Figure 18. Recharge Transistor Turn-off Propagation Delay vs. Temperature, VBS=7V**



**Figure 19. High Side Turn-off to Recharge Gate Turn-on vs. Temperature, VBS=7V**

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International  
**IR** Rectifier

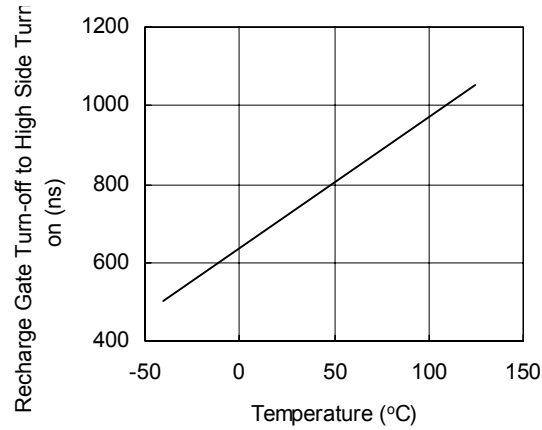
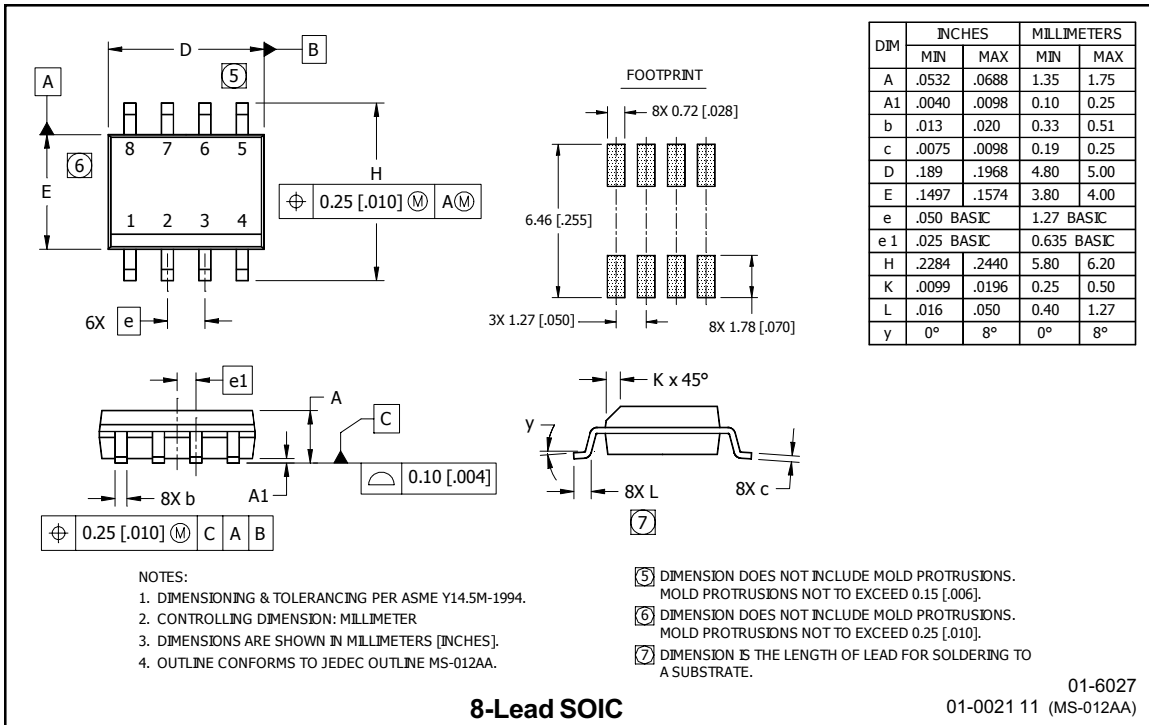


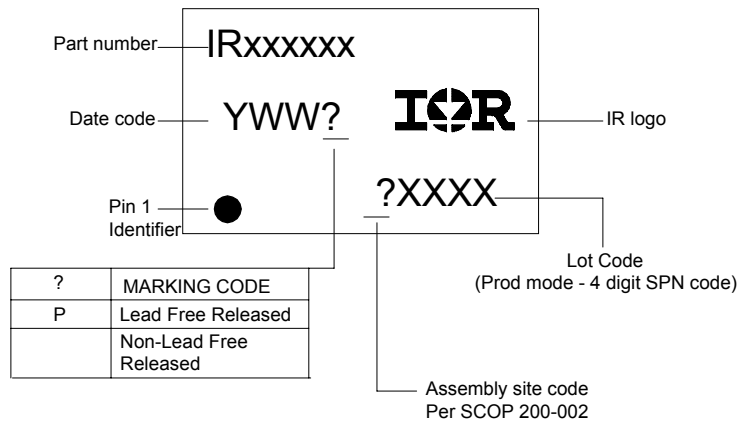
Figure 20. Recharge Gate Turn-off to High Side Turn-on vs. Temperature, VBS=7V

## Case outline



8-Lead SOIC

## LEADFREE PART MARKING INFORMATION



## ORDER INFORMATION

### Basic Part (Non-Lead Free)

8-Lead SOIC IR20153S order IR20153S

### Leadfree Part

8-Lead SOIC IR20153S order IR20153SPbF